

Performance of irradiated Digital Pixel Test Structures produced in 65 nm TPSCo CMOS process

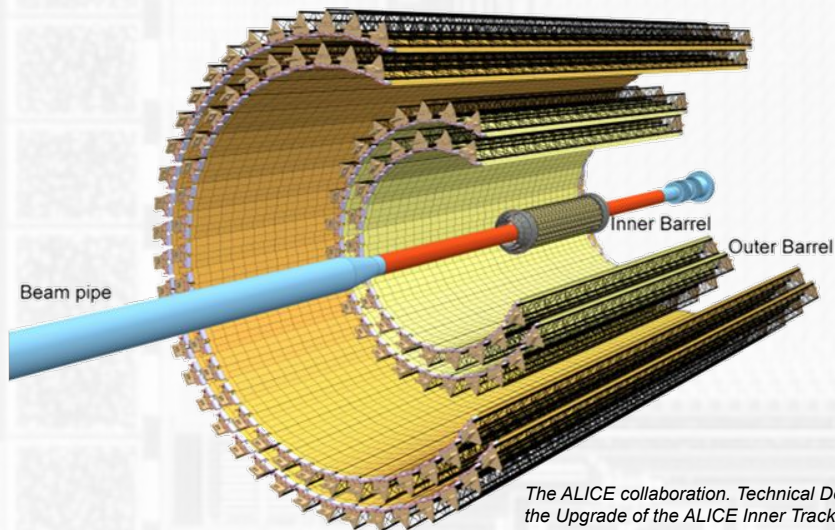
Pascal BECHT (Physikalisches Institut)

High-RR bi-weekly seminar

31 May 2023

From ALPIDE to a 65 nm CMOS MAPS prototype: ALICE inner tracker upgrades

- ITS2 installed for improved tracking resolution and rate capability in LHC Run 3
- Especially true for low-momentum particles (new regions accessible)



The ALICE collaboration. Technical Design Report for the Upgrade of the ALICE Inner Tracking System. J. Phys. G 41 (2014) 087002

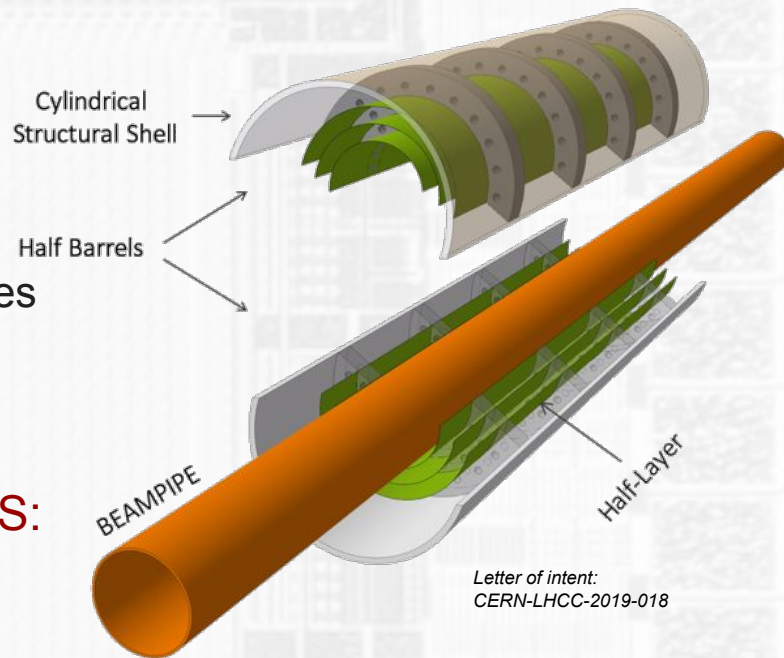
- Powered by state-of-the-art MAPS
- **ALPIDE (180 nm technology node)**
 - ~500k pixels
 - ~30 μm x 30 μm pitch
 - In-pixel signal discrimination, i.e. digital output
 - Spatial resolution better than 5 μm
 - Optimised for low-power consumption
 - 50 μm thin chip

From ALPIDE to a 65 nm CMOS MAPS prototype: ALICE inner tracker upgrades

- Further improvement on material budget possible (wrt. ITS2 with ALPIDE sensors)
 - Improve pointing resolution by factor 2
 - Improve tracking of low momentum particles
- Get closer to the interaction point

• Move to truly-cylindrical, wafer-scale MAPS: ITS3

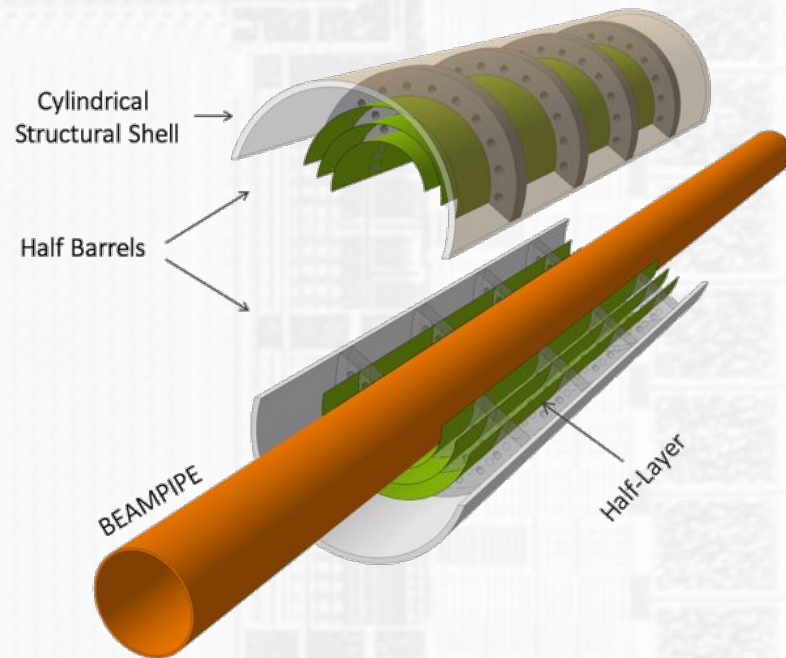
- Sensors self-supported due to bending
- Thin sensors $O(30 \mu\text{m})$
- Cooled by air flow
- Optimised power consumption



- New generation of tracking detectors
- R&D started on new sensors to face the challenges

From ALPIDE to a 65 nm CMOS MAPS prototype: A new sensor for the ITS3

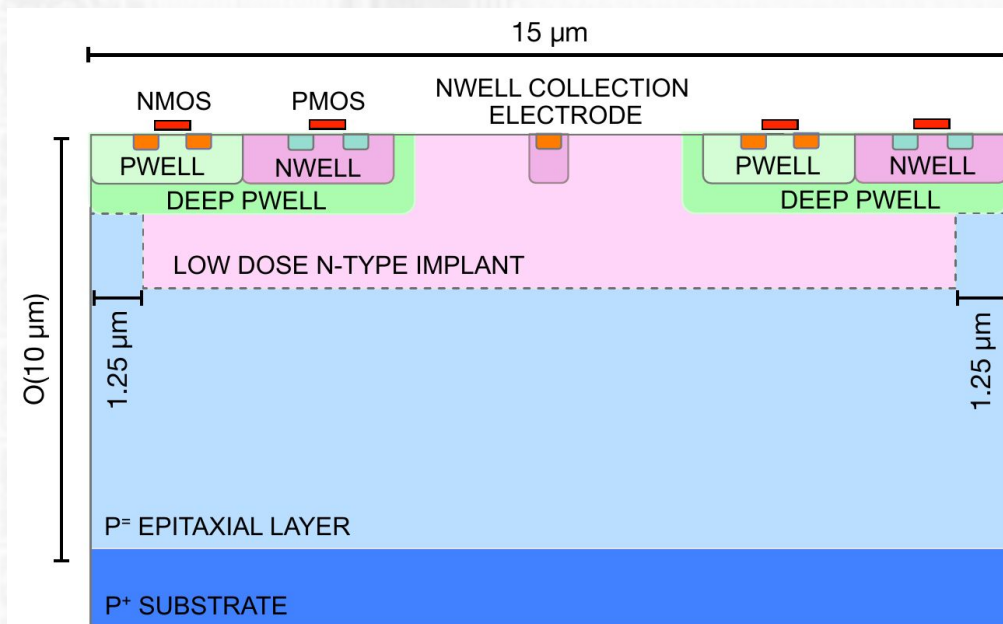
- **65 nm CMOS technology node is key**
 - Larger available wafers (30 cm)
 - Stitching available for production of large area sensors
- **Smaller feature size**
 - Realise smaller pixels with in-pixel signal processing
 - Manageable occupancy at high track densities
- Small scale prototypes are available since 2021
- **Multi Layer Reticle 1 (MLR1) submission**
 - Joint effort of CERN EP R&D and ALICE ITS3



The MLR1 Digital Pixel Test Structure (DPTS)



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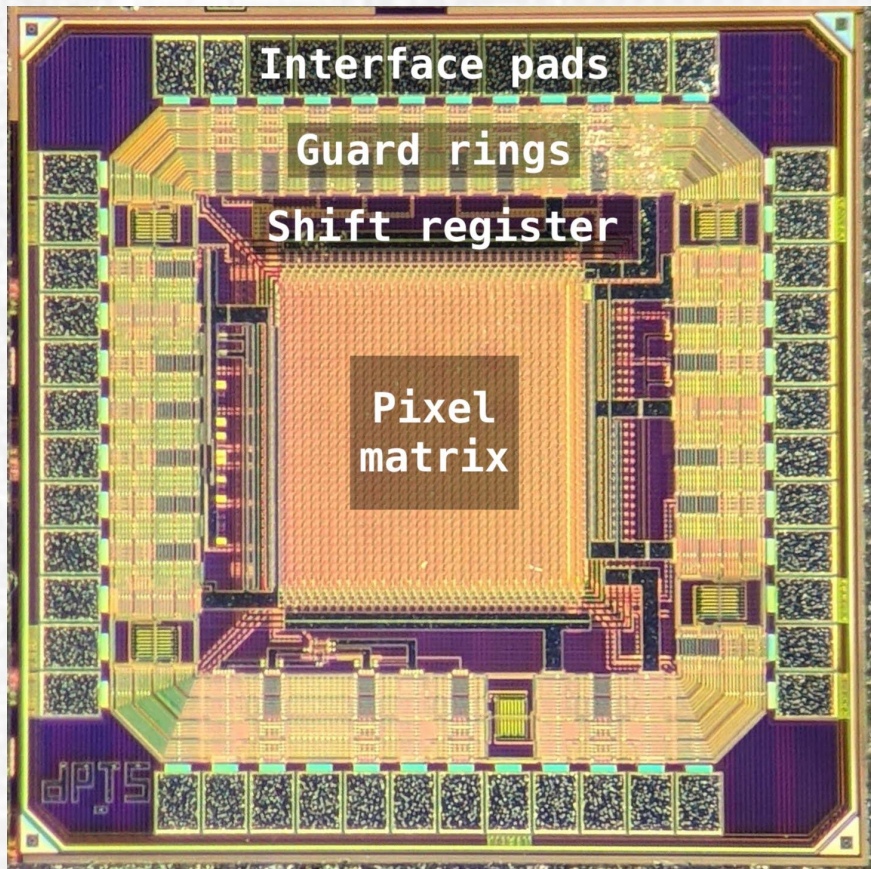
- Produced in “modified process”
- Pixel cross section not to scale

- Active epitaxial layer of $\sim 8 \mu\text{m}$
- Deep n-implant to fully deplete epitaxial layer
- Gaps for having a lateral field component
- Enhance charge collection in a single pixel
- Higher operating margin due to larger seed pixel signal

The MLR1 Digital Pixel Test Structure (DPTS)

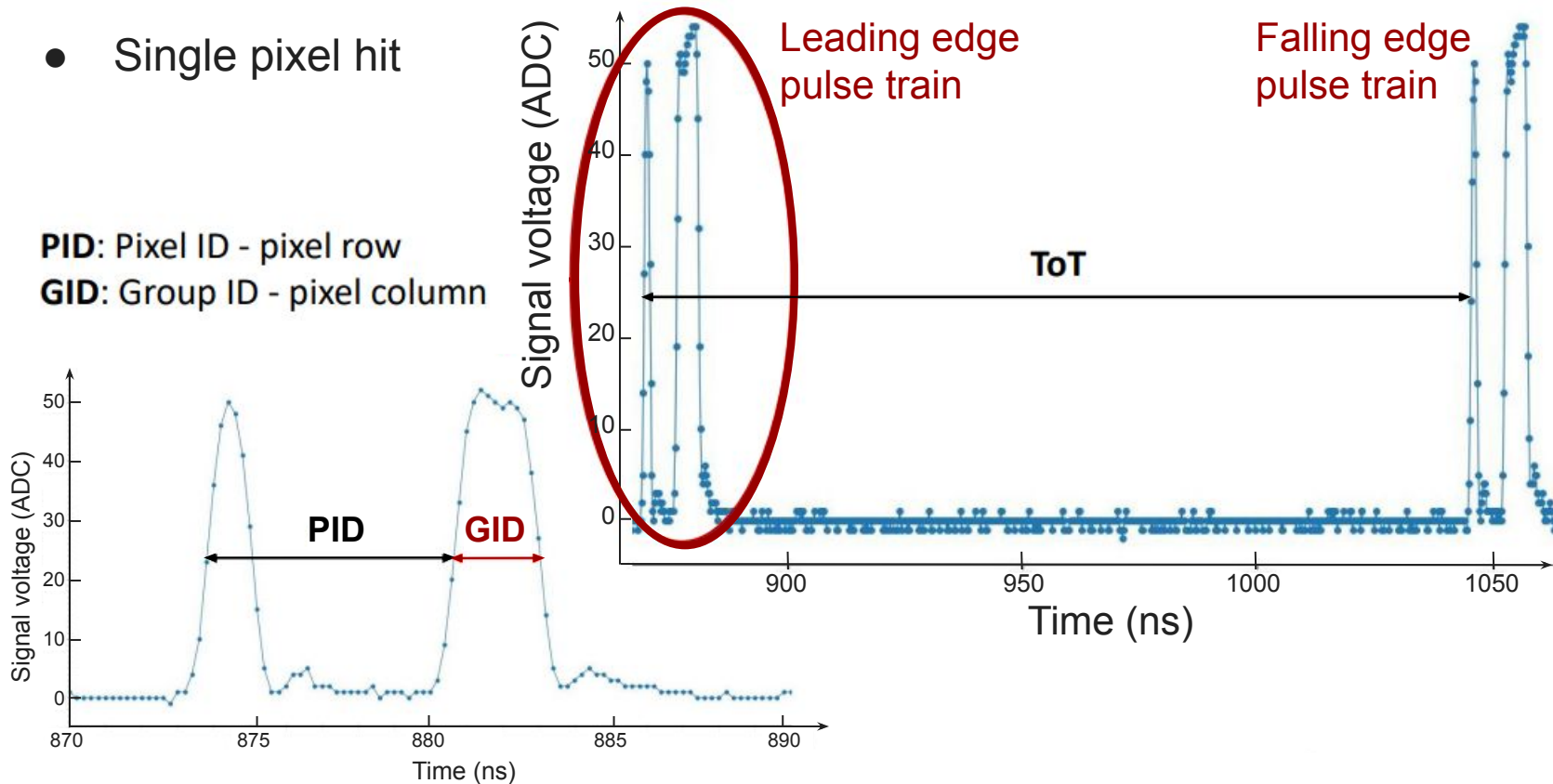


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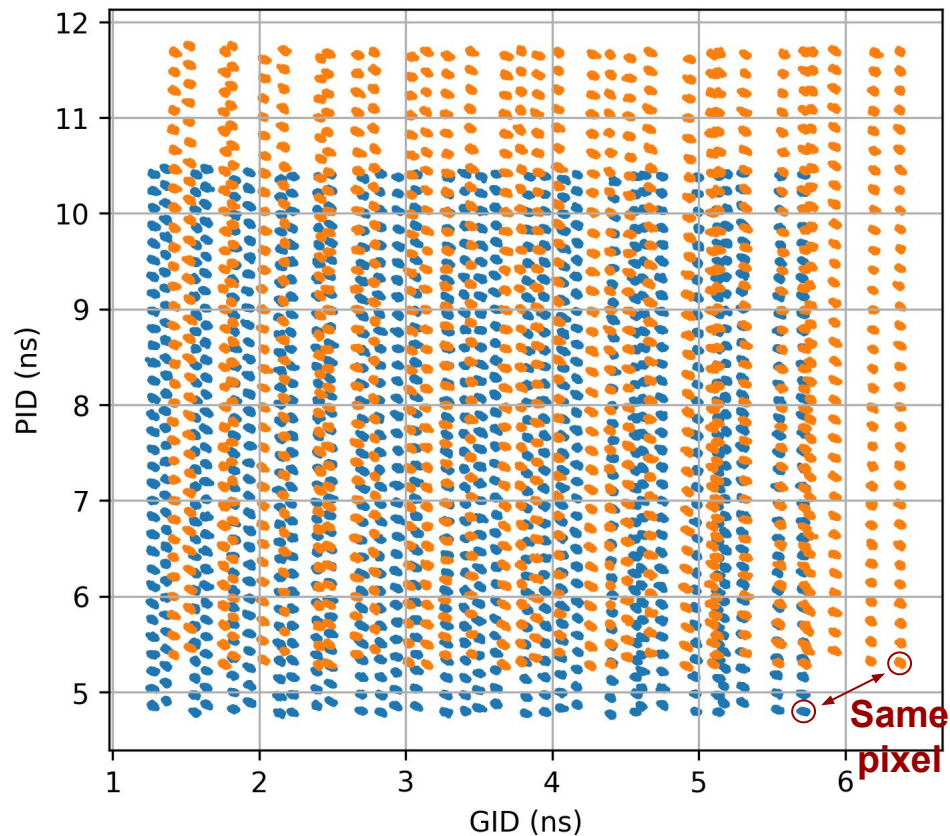
- Full pixel matrix with **in-pixel signal discrimination**
 - Test front-end and digital building blocks
 - In-beam sensor performance characterisation
- 480 μm x 480 μm active area
- **32 x 32 pixel (15 μm x 15 μm)**
- Asynchronous digital readout (single output line)
- **Time-encoded position information**
- **Access to signal time over threshold**

DPTS signals and position decoding



- Multiple pixel hits may cause signal collisions

DPTS signals and position decoding

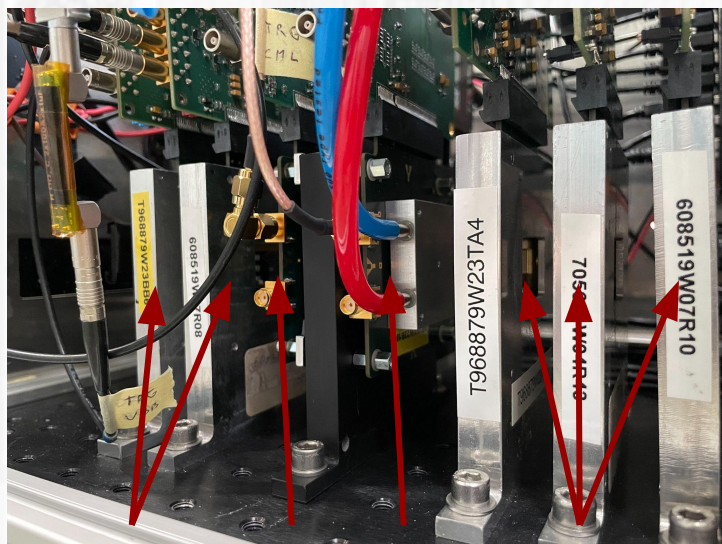


- $V_{sub} = -1.2$ V
- $V_{sub} = -3.0$ V

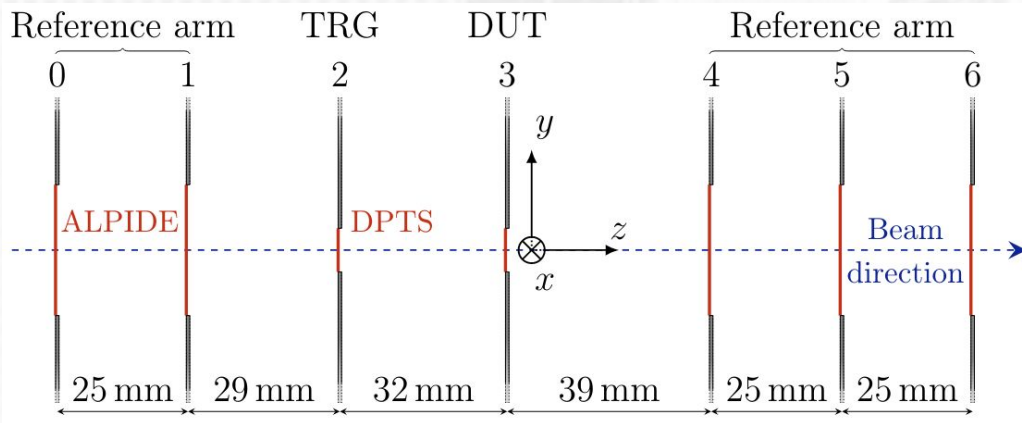
- Position decoding calibration via pulsing
 - One (GID,PID)-point per pixel
- Calibration map strongly depends on back-bias voltage and temperature
 - PID: ~ 0.04 ns / 5°C
 - GID: ~ 0.02 ns / 5°C
- Temperature control needed for reliable decoding

Multiple testbeam campaigns

- DESY
- CERN PS
 - 10 GeV/c
positive hadrons



ALPIDEs TRG DUT ALPIDEs

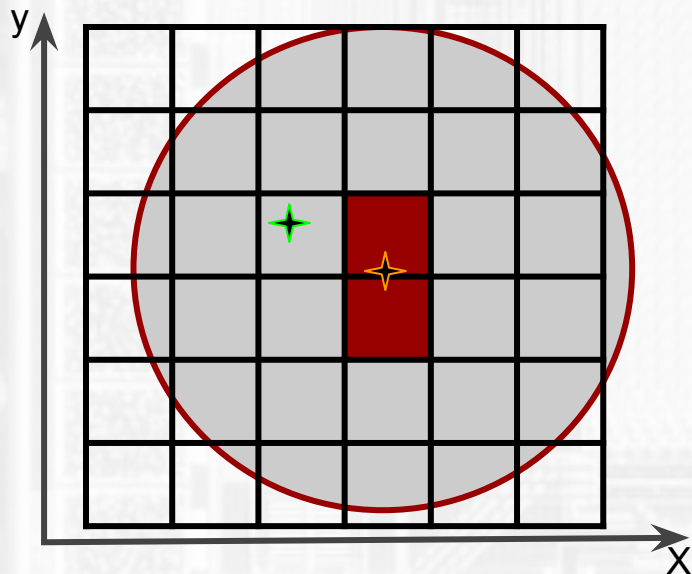
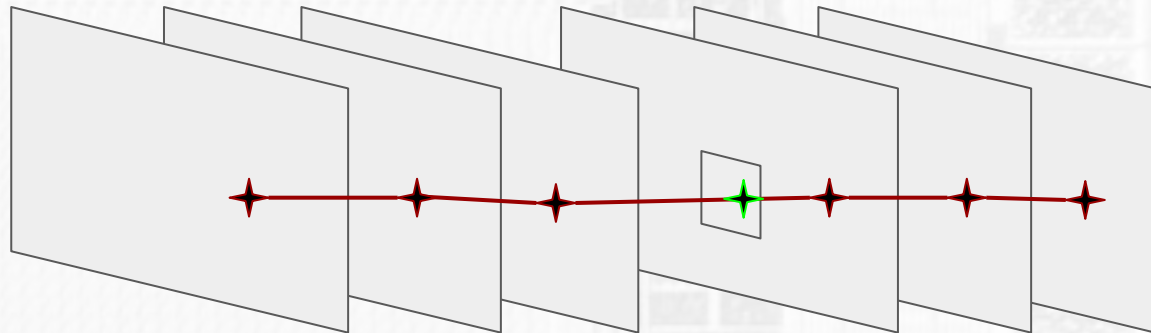


- Temperature kept at 20°C with chiller
- In-situ fake hit rate, threshold measurements
- In-situ position decoding calibration
- DPTS waveforms read out with oscilloscope
- Data analysis with Corryvreckan
 - Alignment, Tracking, DUT association
 - <https://gitlab.cern.ch/corryvreckan/corryvreckan>



Testbeam data analysis

- Track fitting from reference planes
- GBL model used
- Multiple scattering taken into account
- **Interpolation** to DUT
- Associate **measured DUT cluster**



Efficiency calculation

- No spatial window
 - Undecodable events considered: “Signal clash”
 - Trigger mitigates false hit associations
- Time window: 1.5 μ s
- Number-ratio of **matched tracks** and total reconstructed tracks

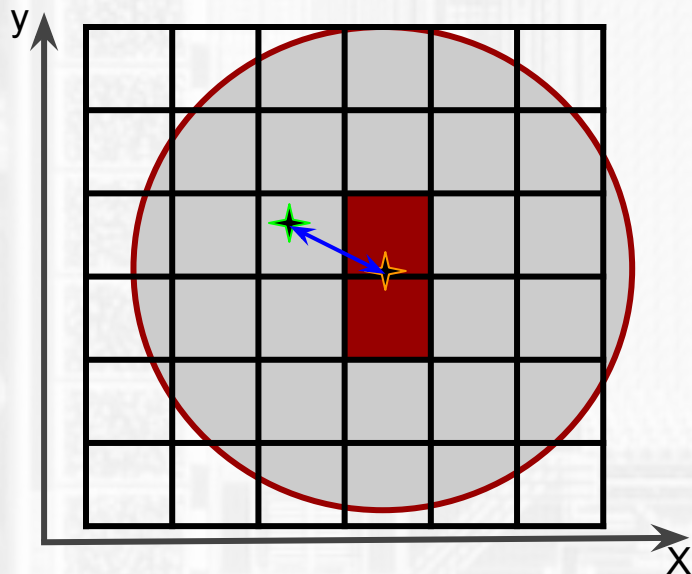
Testbeam data analysis



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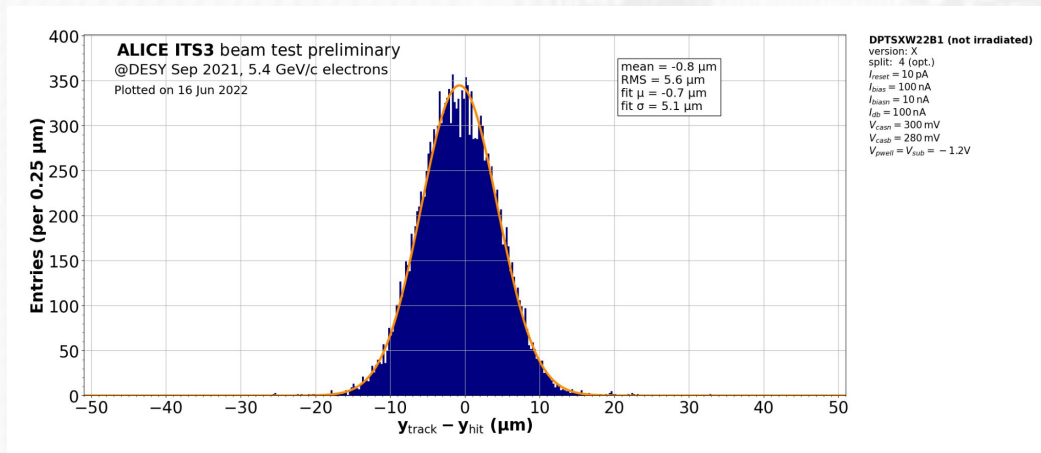


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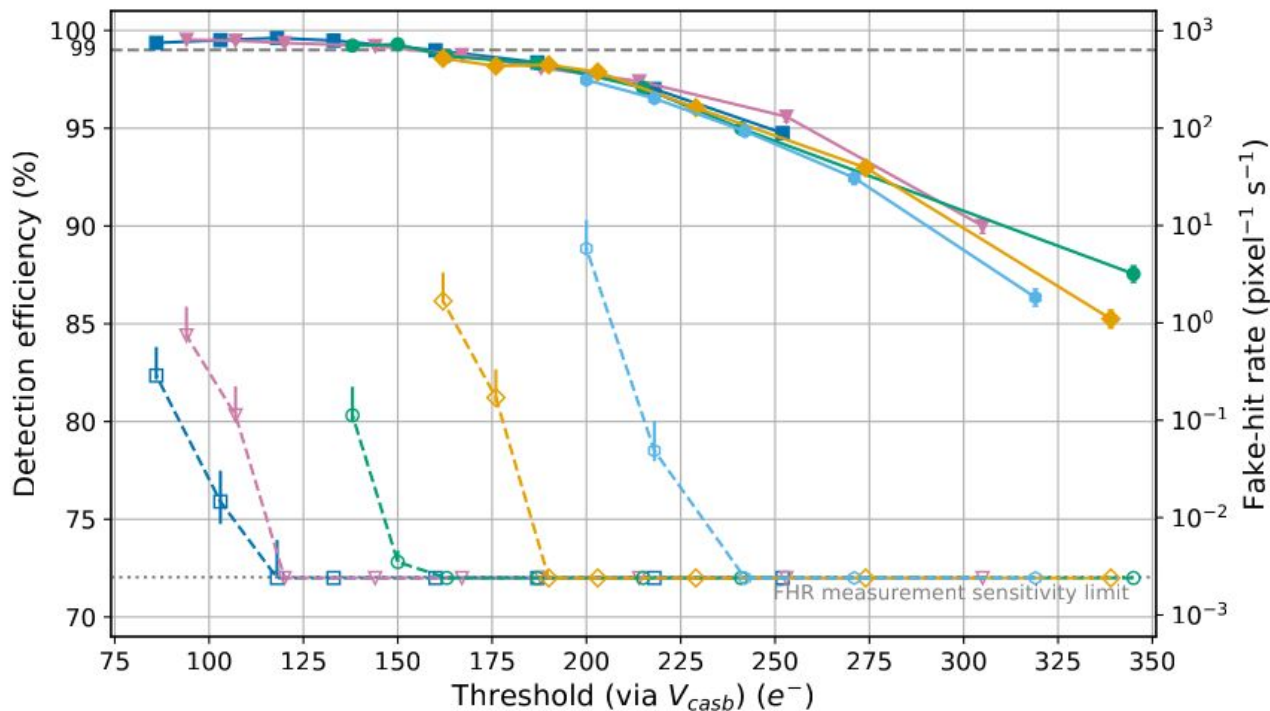
Position resolution calculation

- Spatial window: $45\ \mu\text{m}$ (3 px)
- Time window: $1.5\ \mu\text{s}$

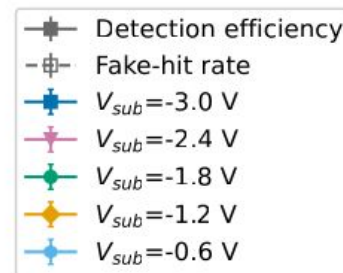


- Width of **spatial residual distribution** in x and y
 - Arithmetic mean
- Subtract telescope resolution from simulation: $2.43\ \mu\text{m}$

DPTS performance - Detection efficiency Dependence on back-bias voltage (VBB)



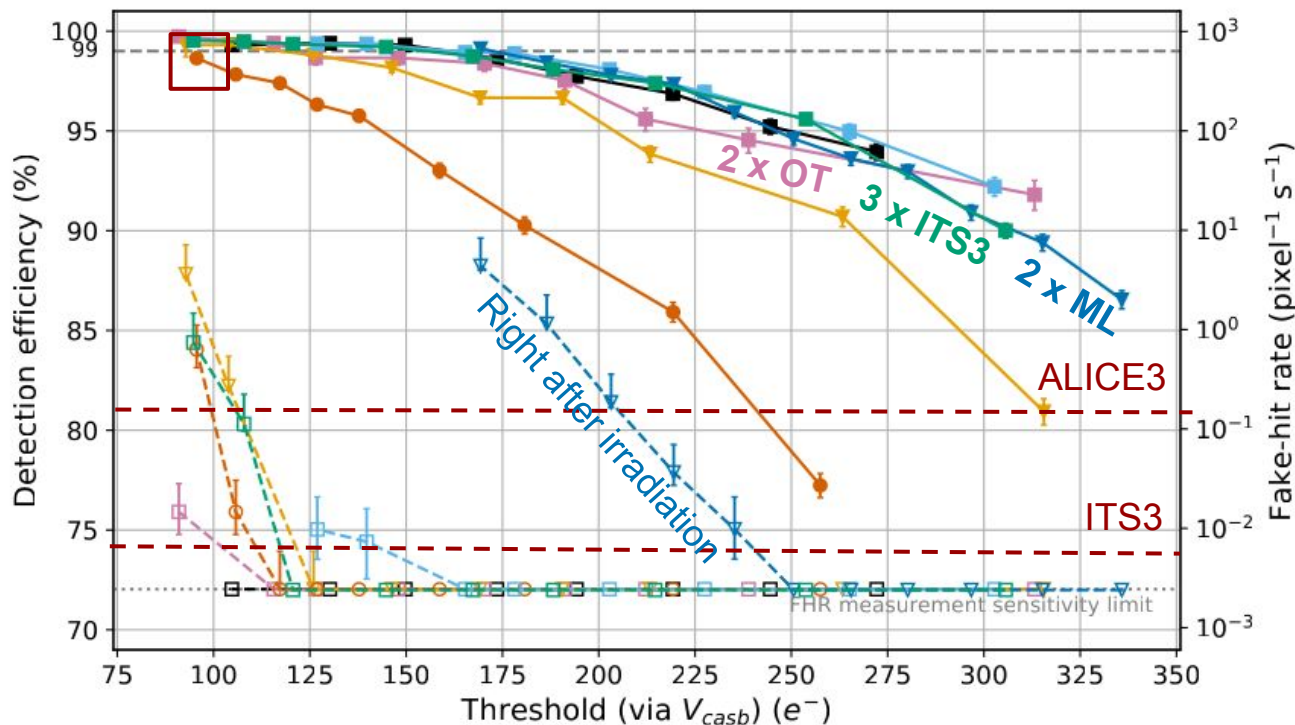
DPTS @ 10 kGy +
 10^{13} 1 MeV n_{eq} cm⁻²



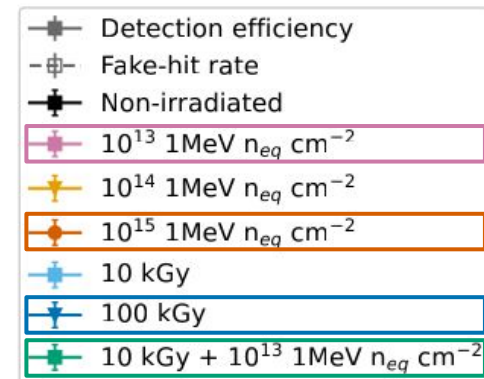
Association window:
480 μ m x 1.5 μ s

- Detection efficiency exceeds 99% for a wide range of working points
- Manageable noise levels
 - FHR increase with lower VBB

DPTS performance - Detection efficiency Irradiated sensors



DPTS @ 20 °C (no cooling)



Association window:
480 μ m x 1.5 μ s

- DPTS stays efficient across different irradiation levels
- ITS3 radiation hardness requirement fulfilled

DPTS performance - Origin of detection efficiency loss

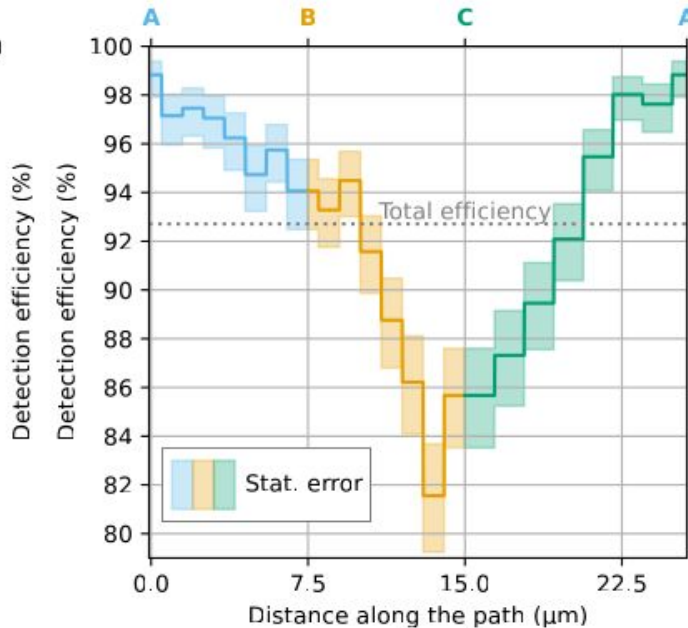
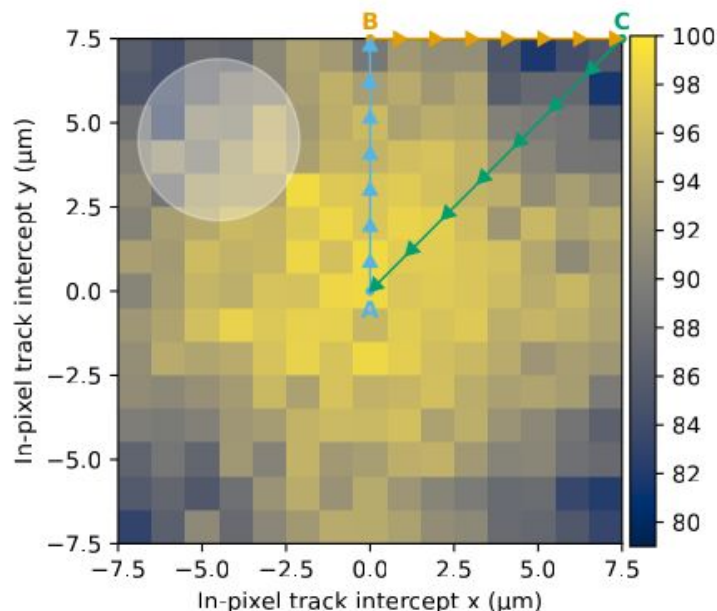


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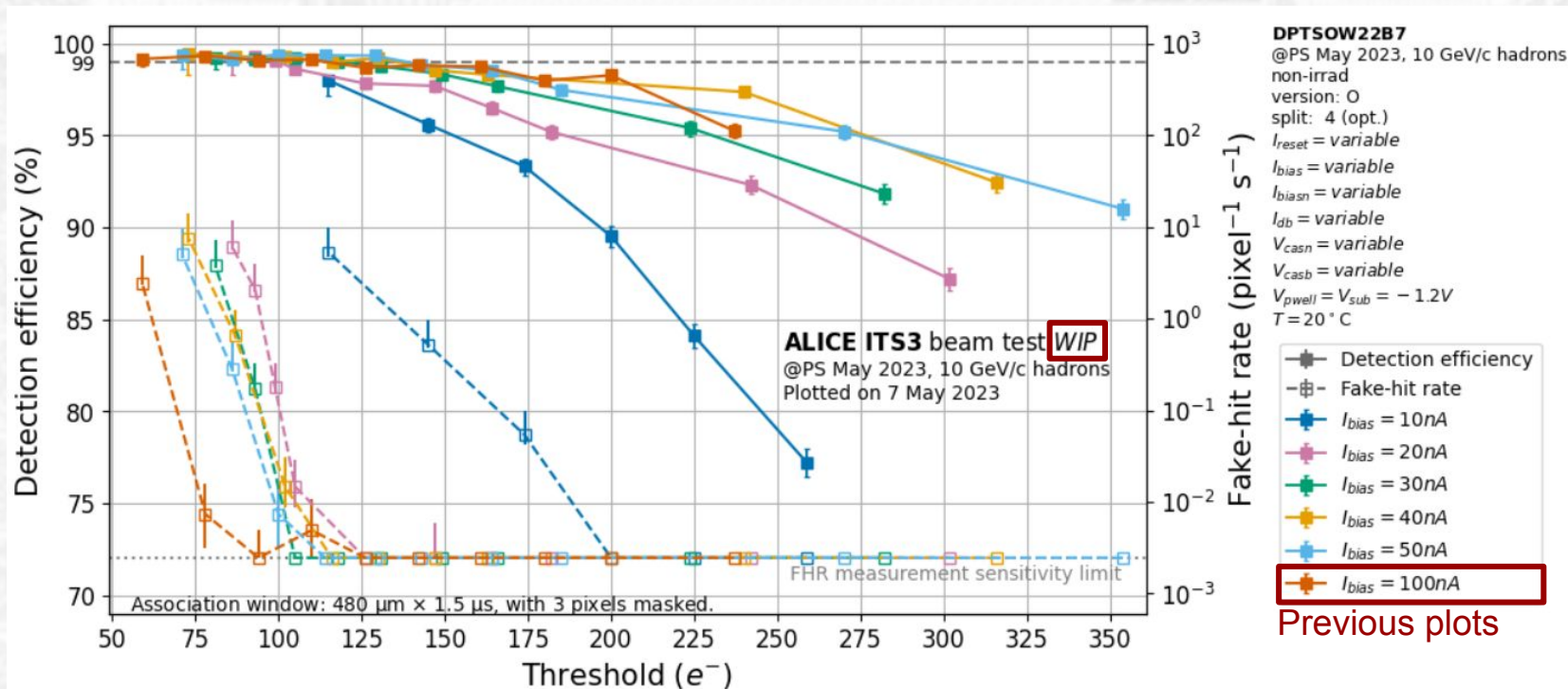


- Lower detection efficiency with increasing distance to the collection diode
- Similar observation for non-irradiated sensor at **higher** threshold values

- Highest NIEL fluence:
 $10^{15} \text{ 1 MeV } n_{\text{eq}} \text{ cm}^{-2}$
- Intermediate threshold:
155 electrons
- 2.4 μm track intercept uncertainty

DPTS performance - Detection efficiency

Non-irradiated sensor vs. power consumption



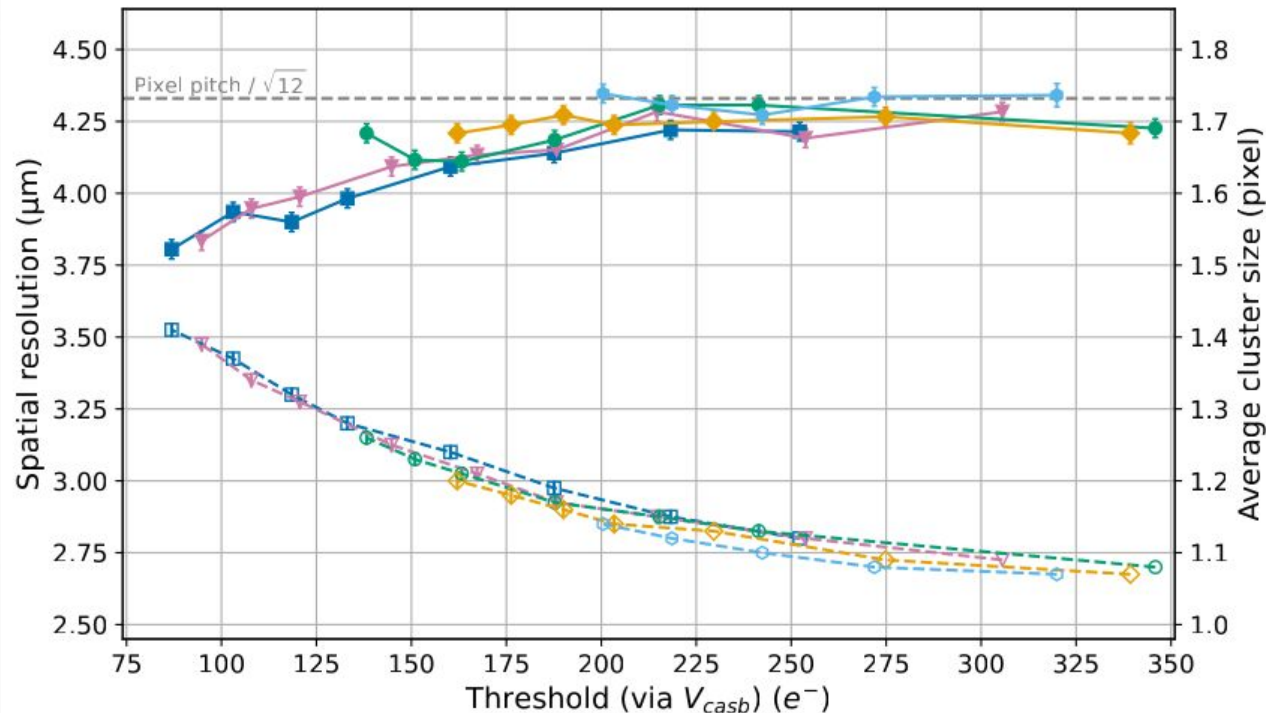
- Worse noise performance with lower power consumption (IBIAS)
- Lower power consumption possible
 - IBIAS=10/20 nA not performant

DPTS performance - Spatial resolution

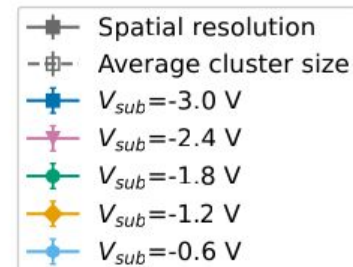
Dependence on back-bias voltage (VBB)



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DPTS @ 10 kGy +
 $10^{13} \text{ 1 MeV } n_{eq} \text{ cm}^{-2}$

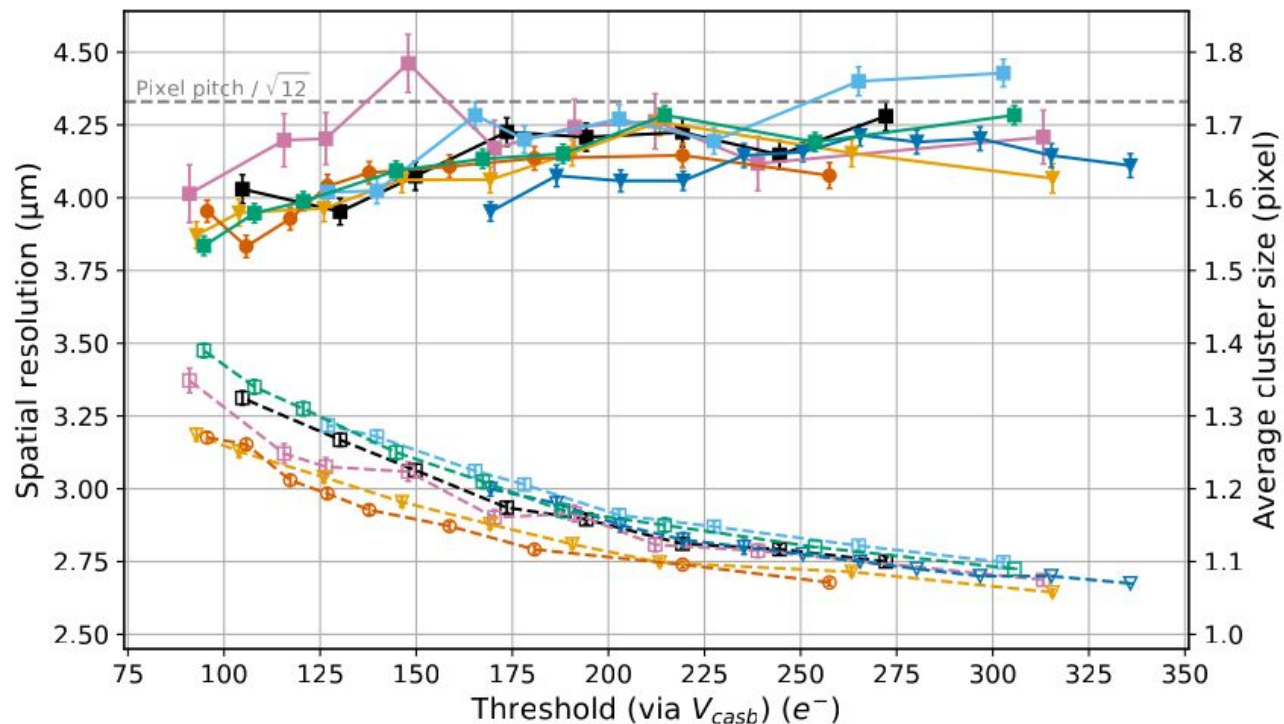


Association window:
 $45 \mu\text{m} \times 1.5 \mu\text{s}$

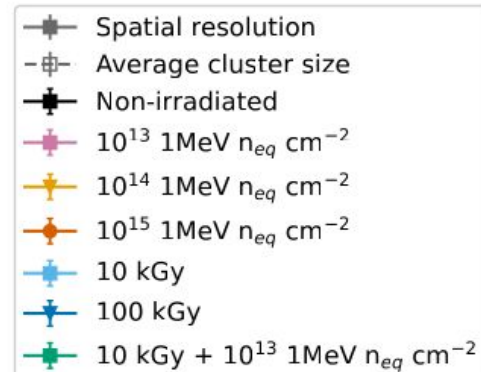
- Dominated by small pixel size
- Spatial resolution improves with increasing cluster size

DPTS performance - Spatial resolution

Irradiated sensors



DPTS @ 20 °C (no cooling)



Association window:
45 μm x 1.5 μm

- No strong dependence on irradiation level
- Visible cluster size ordering according to NIEL dose

Summary and Outlook



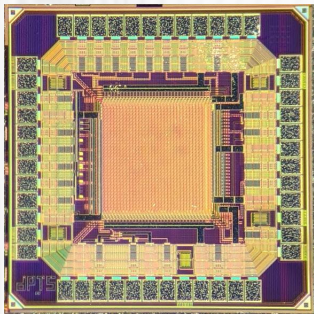
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- 65 nm CMOS technology qualified for MAPS • used in particle/nuclear physics
- In-beam characterisation of irradiated DPTS • sensors



- Operational range for high irradiation levels up to: 100 kGy and $10^{15} \text{ 1 MeV } n_{\text{eq}} \text{ cm}^{-2}$
 - At room temperature!
 - Still reaches 99% detection efficiency
- Spatial resolution matches expectation

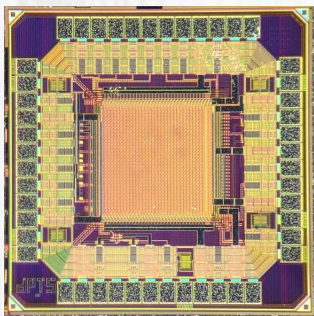
DPTS characterisation paper
<https://arxiv.org/abs/2212.08621>

Additionally covers:

- Full electrical characterisation
- ^{55}Fe response
- Timing resolution
- New testbeam measurements:
 - Performance vs. power consumption (ongoing)
 - Last ingredient for TDR
- Bending of DPTS sensors in progress
 - ↓ Excellent results from MLR1 submission
- Engineering run with stitched sensors
 - Sensors have arrived at CERN

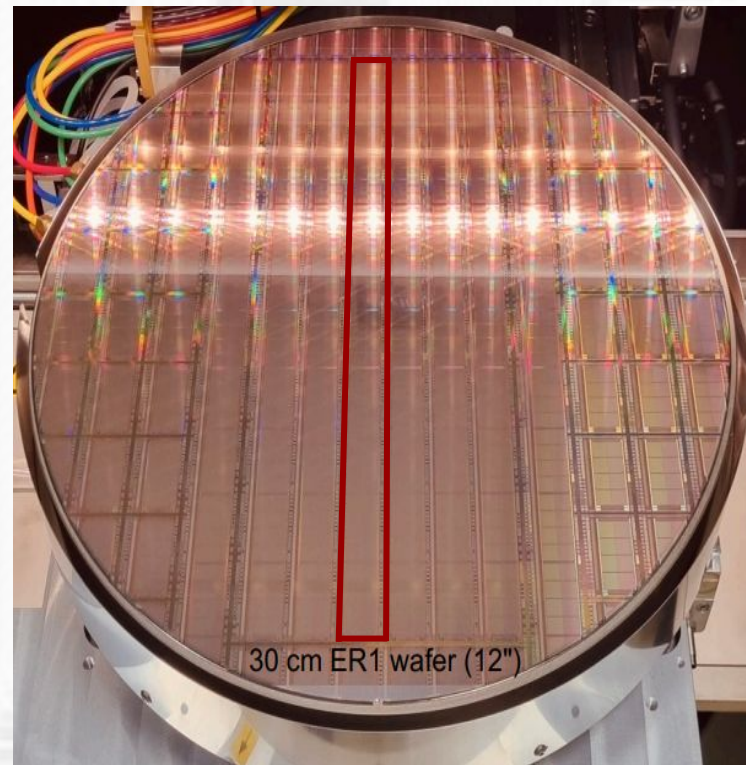
Summary and Outlook

- 65 nm CMOS technology qualified for MAPS used in particle/nuclear physics
- In-beam characterisation of irradiated DPTS sensors



- Operational range for high irradiation levels up to: 100 kGy and $10^{15} \text{ 1 MeV } n_{\text{eq}} \text{ cm}^{-2}$
 - At room temperature!
 - Still reaches 99% detection efficiency
- Spatial resolution matches expectation

- The show must go on:



- First stitched sensors are alive



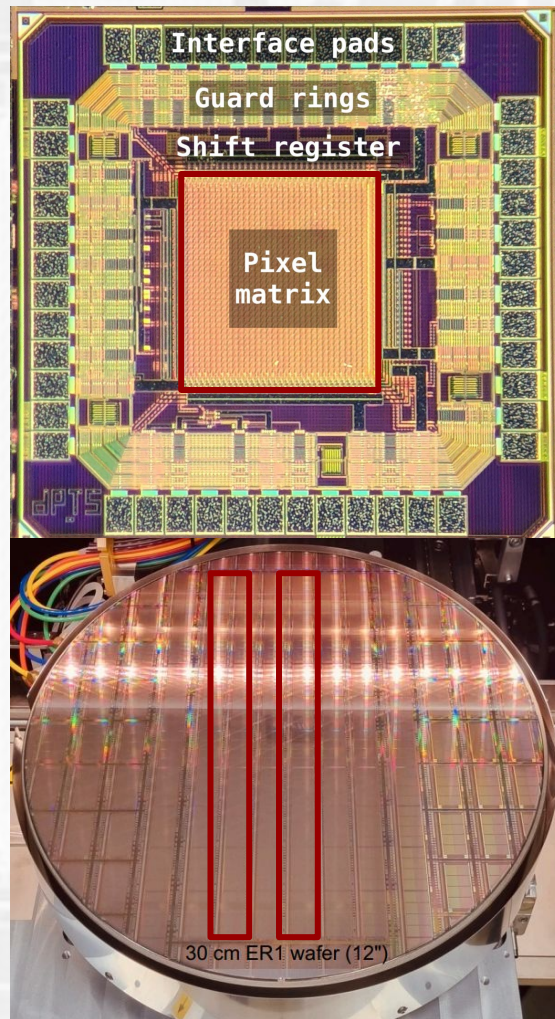
Auxiliary slides

The next ALICE inner tracker upgrade: sensors

- Improve tracking performance by reduction of material budget
 - E.g. pointing resolution by factor 2
 - Especially in low-momentum regime
- Truly cylindrical pixel detector wrapped around the beam pipe
 - Closer to interaction point
 - Less mechanical support
 - New beam pipe
- Cooled by airflow
- Waferscale sensors

ITS3 implies change to 65 nm CMOS technology node

- 30 cm diameter wafers, stitching possible
- Small pixel/feature size (occupancy)
- Two submissions so far (MLR1, ER1)



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Digital Pixel Test Structure (DPTS)

- 32x32 px
- 15 μm pitch
- 480 μm x 480 μm

Monolithic Stitched Sensor (MOSS)

- 6.72 Mpx
- 18/22.5 μm pitch
- 1.4 cm x 25.9 cm

The schematic diagram illustrates a 1T1C readout circuit, divided into two main functional blocks: **Amplification and reset** and **Discrimination**.

Amplification and reset: This block contains the input stage and the amplifier. The input signal is coupled to the gate of transistor M1 through a coupling capacitor C_{inj} (160 aF) and a collection diode connected to a substrate (SUB) terminal. The input signal is also connected to the gates of M2 and M3. Transistors M0, M1, M2, and M3 form a differential pair. The gates of M0 and M1 are biased by IBIAS, while the gates of M2 and M3 are biased by IBIASN. The sources of M0 and M1 are connected to AVDD, and the sources of M2 and M3 are connected to ground. The output of this stage is the **Amplifier output**, which is the differential signal between the drains of M1 and M2.

Discrimination: This block contains the discriminator stage. It consists of a differential pair of transistors M5 and M6, biased by IRESET and VCBASB, and a common source load transistor M7 biased by VCBASN. The output of this stage is the **Discriminator output**, which is the differential signal between the drains of M5 and M6.

The circuit is powered by AVDD and ground. The input signal is represented by a red waveform, and the output signals are also represented by red waveforms.

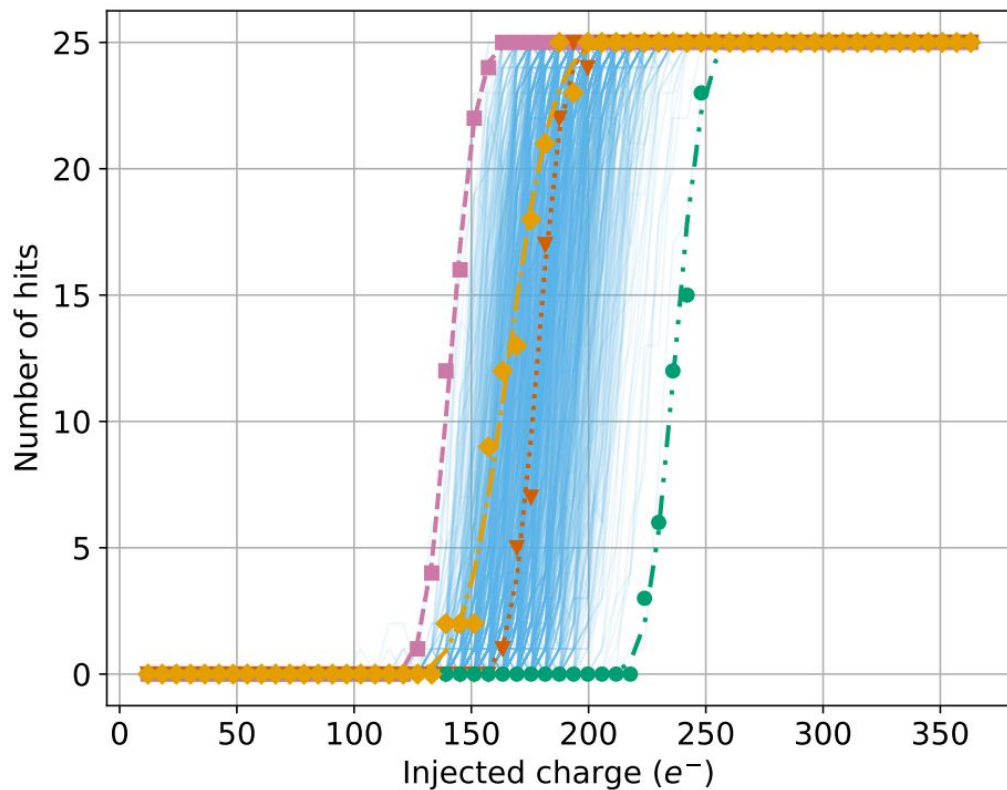
DPTS threshold measurement



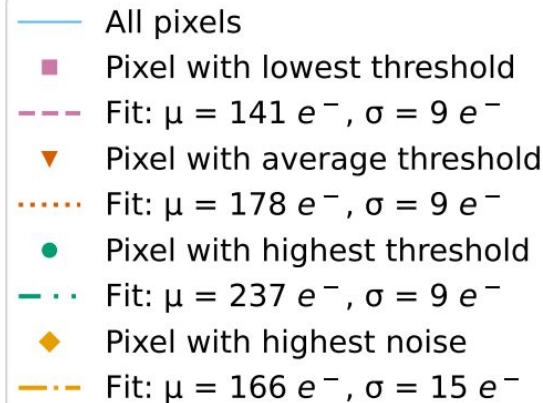
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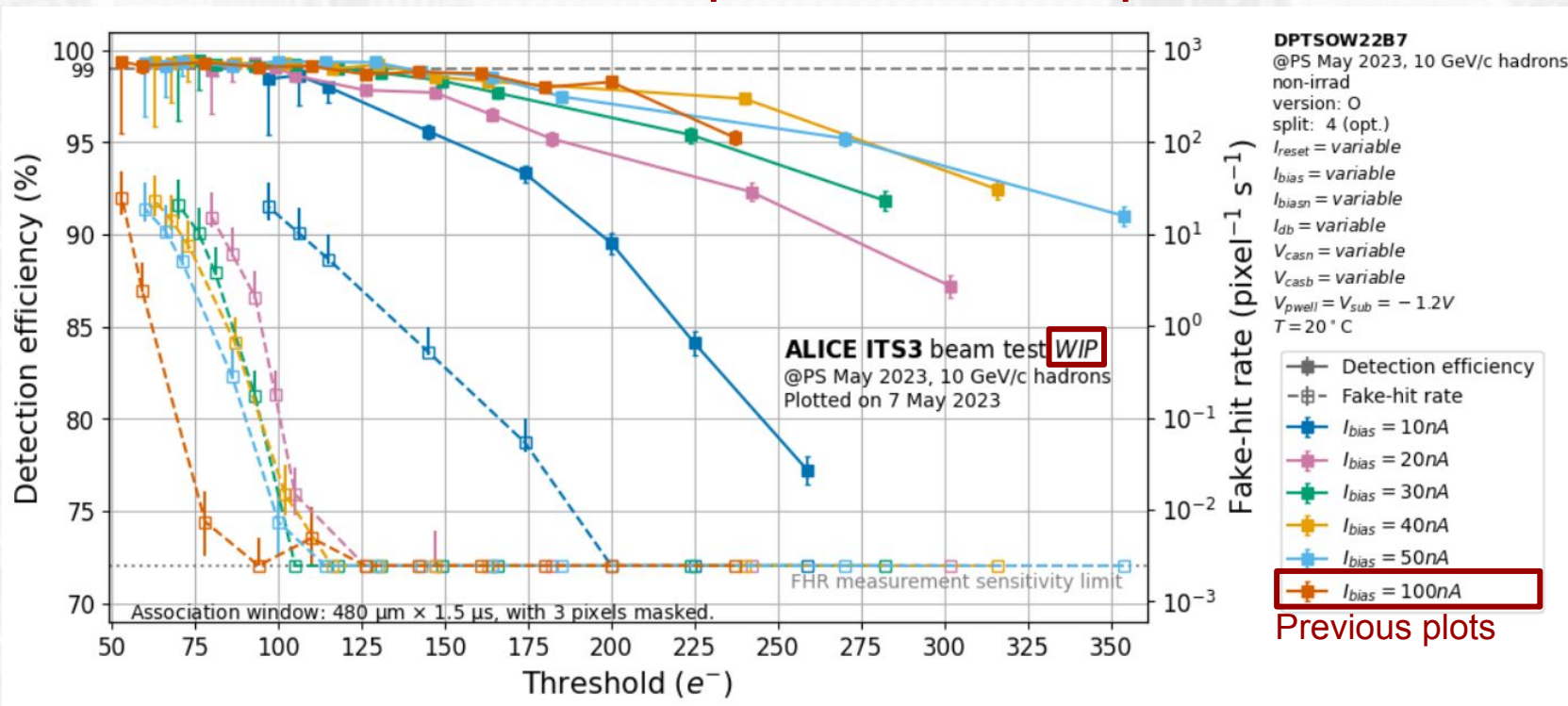


- Tuned to average threshold of 180 e @ VBB -1.2 V



DPTS performance - Detection efficiency

Non-irradiated sensor vs. power consumption



- Worse noise performance with lower power consumption (IBIAS)
- Lower power consumption possible
 - IBAS=10/20 nA not performant

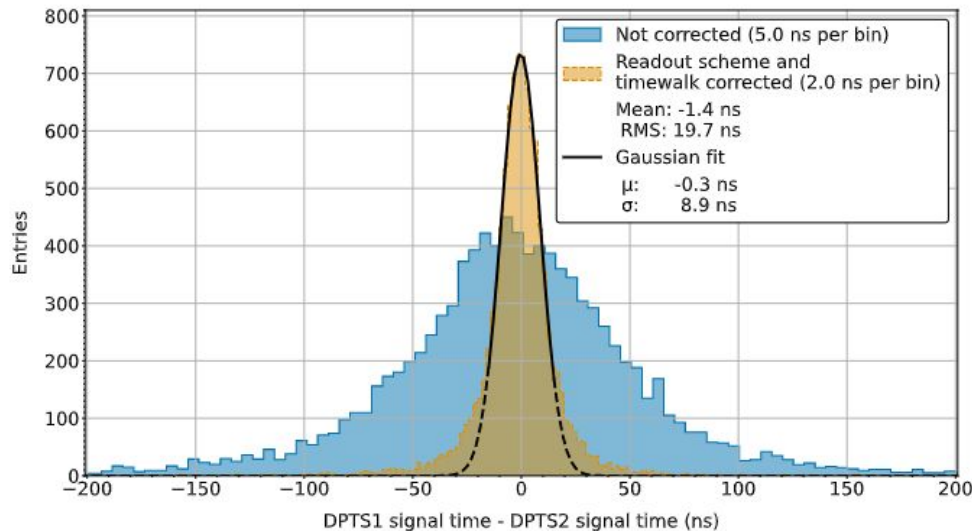
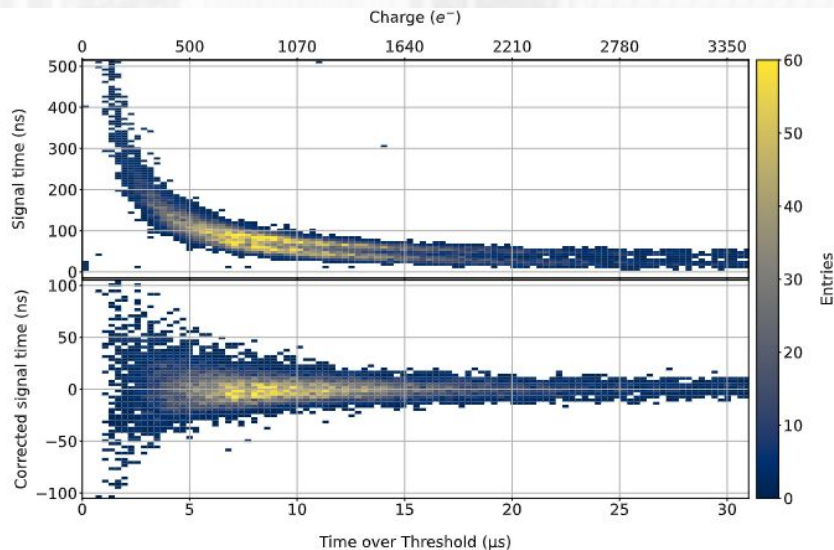
DPTS time resolution



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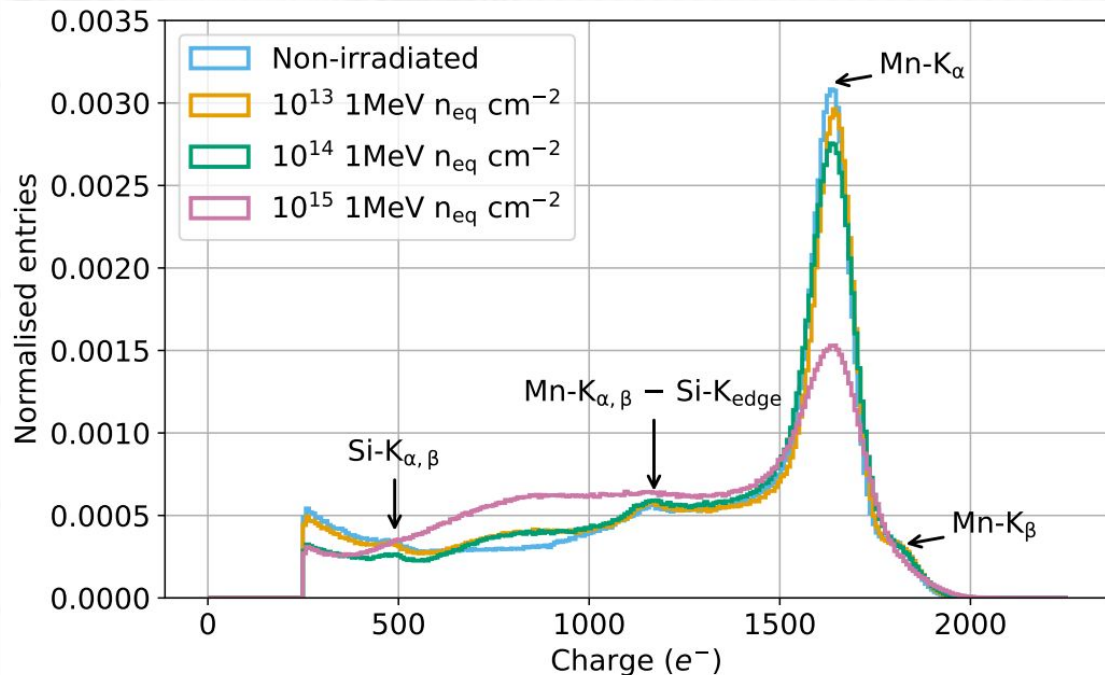
- DESY 5.4 GeV electrons



- Scintillators as absolute timing reference
- Time difference between two DPTS sensors
- Signal time needs to be corrected for:
 - Timewalk
 - Readout scheme

- **Time resolution:**
 6.3 ± 0.1 ns

DPTS energy resolution with Fe55 source measurements



- Energy resolution of Mn- K_{α} peak

Irradiation	Resolution (%)
Non-irradiated	7.50 ± 0.02
10^{13} 1 MeV n_{eq} cm^{-2}	22.4 ± 0.4
10^{14} 1 MeV n_{eq} cm^{-2}	24.5 ± 0.7
10^{15} 1 MeV n_{eq} cm^{-2}	32.7 ± 0.7

- Degradation of the energy resolution points to distortions in the charge collection
 - Charge trapping
 - Modification of the electric fields

ITS3 pointing resolution



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